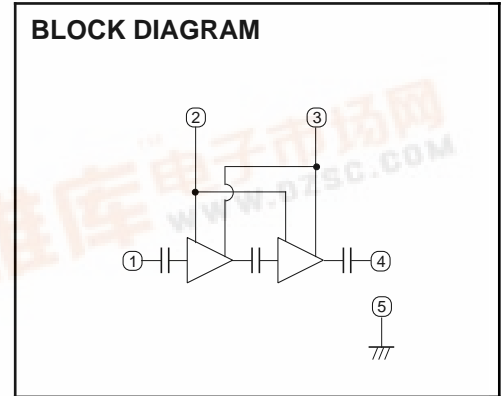
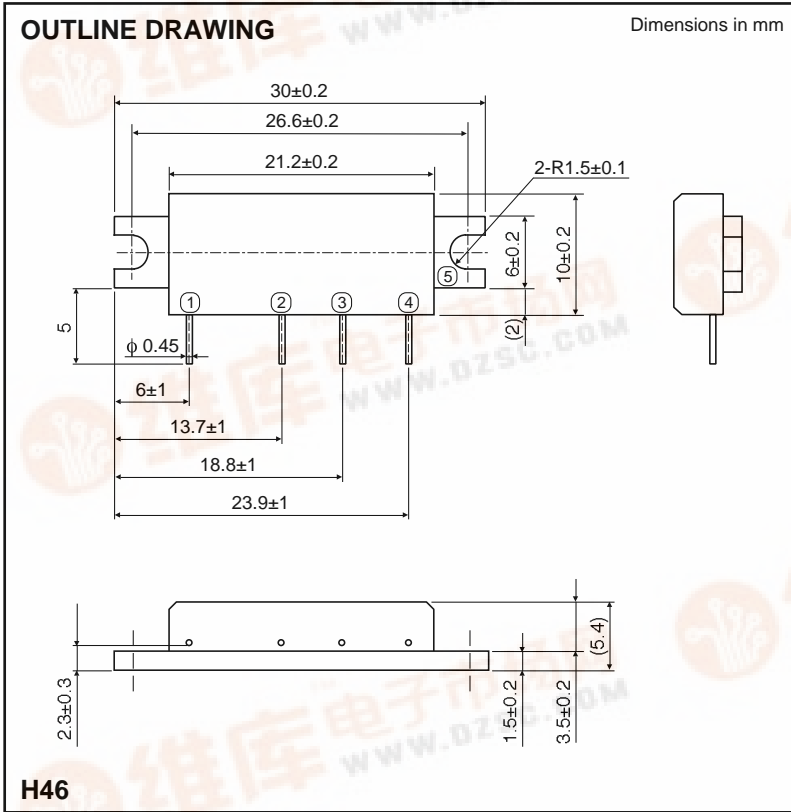


MITSUBISHI RF POWER MODULE

M68710EL

SILICON MOS FET POWER AMPLIFIER, 290-330MHz, 2W, FM PORTABLE RADIO



PIN:

- ①Pin : RF INPUT
- ②VGG : GATE BIAS SUPPLY
- ③VDD : DRAIN BIAS SUPPLY
- ④Po : RF OUTPUT
- ⑤GND: FIN

ABSOLUTE MAXIMUM RATINGS (Tc=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Ratings	Unit
VDD	Supply voltage	VGG 3.5V, ZG=ZL=50	9	V
VGG	Gate bias voltage		4	V
Pin	Input power	f=290-330MHz, ZG=ZL=50	30	mW
Po	Output power	f=290-330MHz, VDD 9V, ZG=ZL=50	3	W
Tc (OP)	Operation case temperature	f=290-330MHz, VDD 9V, ZG=ZL=50	-30 to +110	°C
Tstg	Storage temperature		-40 to +110	°C

Note. Above parameters are guaranteed independently.

ELECTRICAL CHARACTERISTICS (Tc=25°C, ZG=ZL=50 unless otherwise noted)

Symbol	Parameter	Test conditions	Limits		Unit
			Min	Max	
f	Frequency range		290	330	MHz
Po	Output power	VDD=6V, VGG=3.5V, Pin=20mW	2		W
τ	Total efficiency		40		%
2fo	2nd. harmonic			-20	dBc
in	Input VSWR			4	-
-	Stability	ZG=50, VDD=4-9V, Load VSWR<4:1	No parasitic oscillation		-
-	Load VSWR tolerance	VDD=9V, Pin=20mW, Po=3W (VGG adjust), ZL=20:1	No degradation or destroy		-

Note. Above parameters, ratings, limits and test conditions are subject to change.

